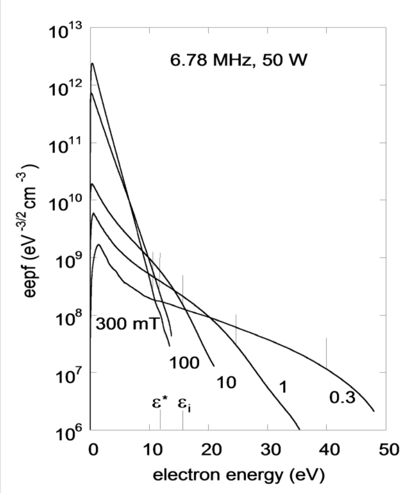
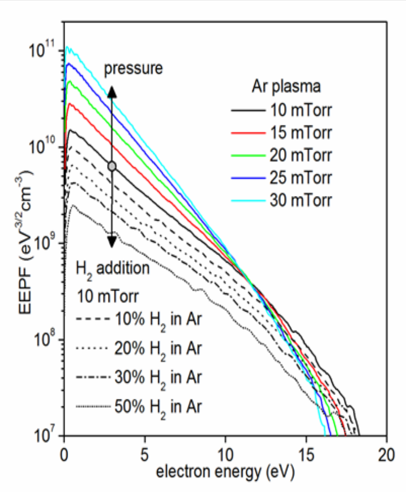
Examples of EEPF measurements with our instruments in basic research and industrial plasmas

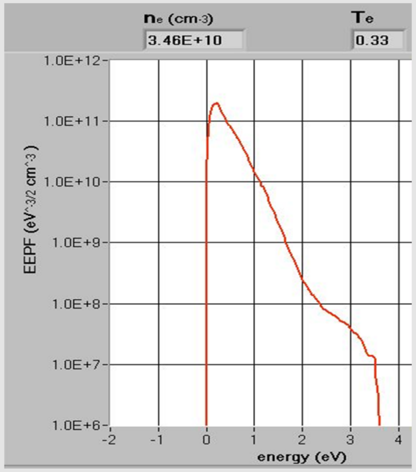
No other probe system provides such energy resolution and dynamic range



EEPF measured in ICP at different Ar pressure. *V. Godyak et al, Plasma Sources Sci. Technol.* ***11****, 525 (2002)*

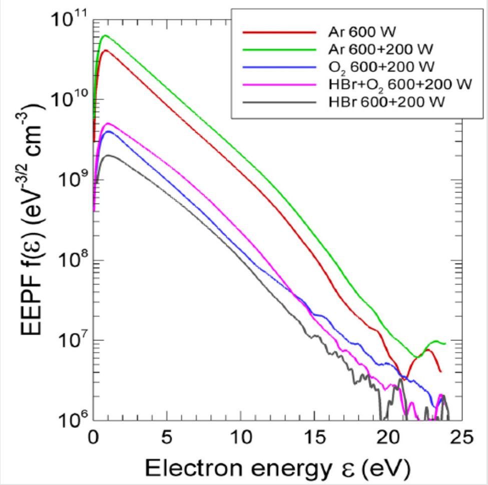


EEPF measured in Ar and Ar/H$_2$ ICP. *N. Fox-lion et al, J. Phys. D: Appl. Phys,.* ***46,*** *485202, (2013)*

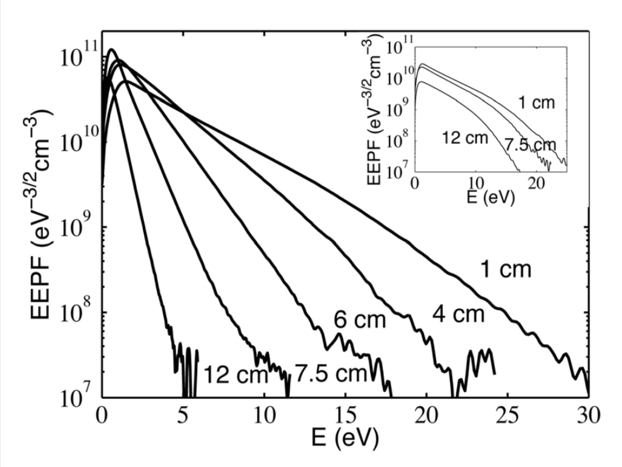


n$_e$ (cm-3) 3.46E+10
T$_e$ 0.33

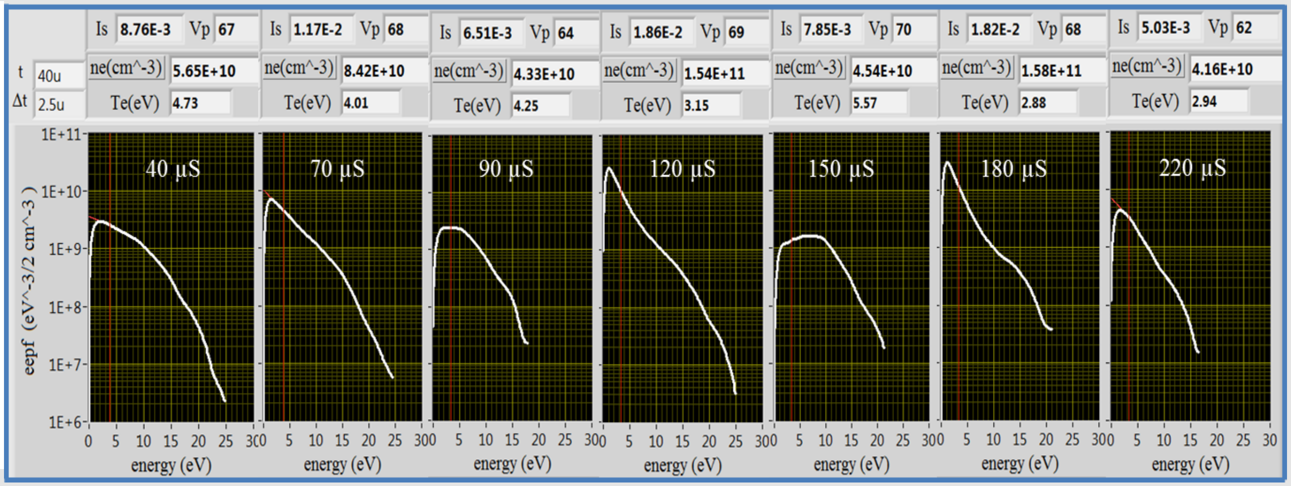
EEPF measured in ECR array reactor, Ar/ SiF$_4$ at 10 mTorr with crystalline silicon deposition. *Ecole Polytechnique, France*



EEPF measured in commercial ICP in different processing mixtures at 15 mTorr. *Mattson Technology, USA*



EEPF space evolution along the magnetic barrier. ICP in Ar at 10 mTorr. *A. Aanesland et al, Appl. Phys. Lett.* ***100****, 044102 (2012)*



t 40u
Δt 2.5u

Is 8.76E-3 Vp 67
ne(cm^-3) 5.65E+10
Te(eV) 4.73

Is 1.17E-2 Vp 68
ne(cm^-3) 8.42E+10
Te(eV) 4.01

Is 6.51E-3 Vp 64
ne(cm^-3) 4.33E+10
Te(eV) 4.25

Is 1.86E-2 Vp 69
ne(cm^-3) 1.54E+11
Te(eV) 3.15

Is 7.85E-3 Vp 70
ne(cm^-3) 4.54E+10
Te(eV) 5.57

Is 1.82E-2 Vp 68
ne(cm^-3) 1.58E+11
Te(eV) 2.88

Is 5.03E-3 Vp 62
ne(cm^-3) 4.16E+10
Te(eV) 2.94

Time evolution of EEPF in the positive column of Ar dc discharge with moving striations. p = 10 mTorr, I$_d$ = 1 A.

V. Godyak et al, Presented at GEC 2014, Raleigh, NC, November 2-7 (2014)

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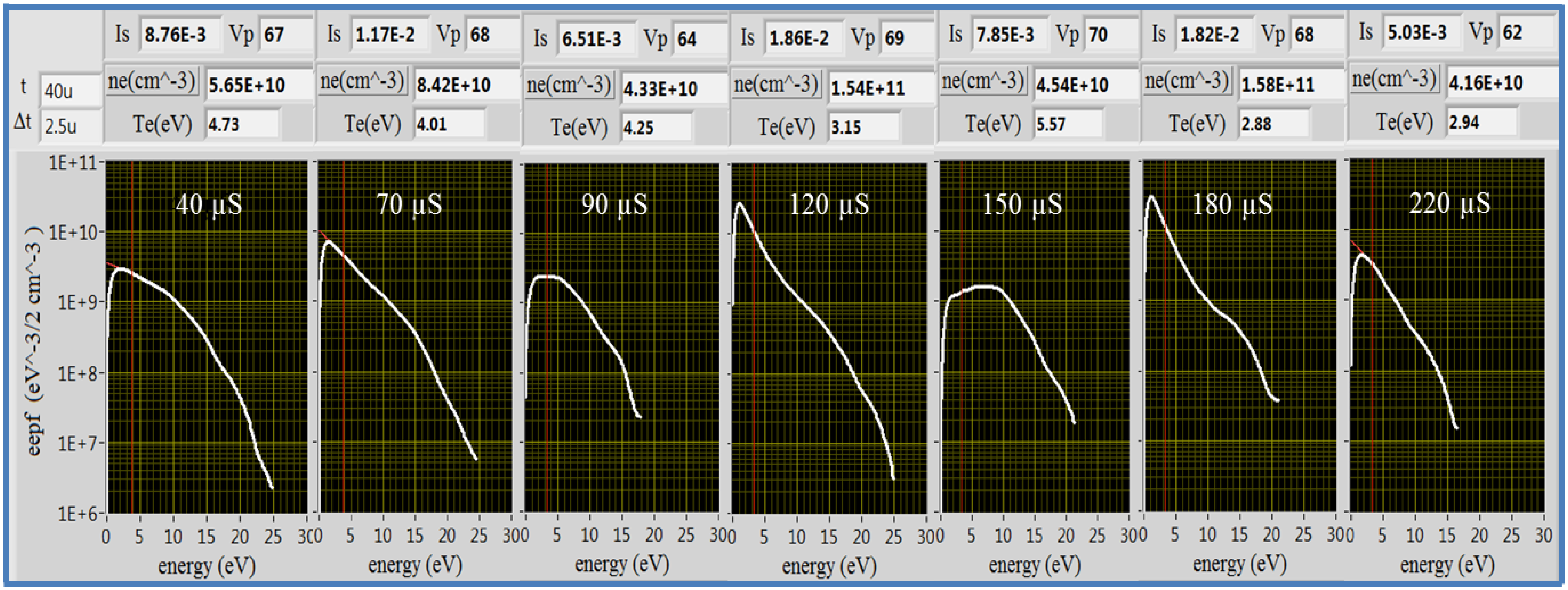


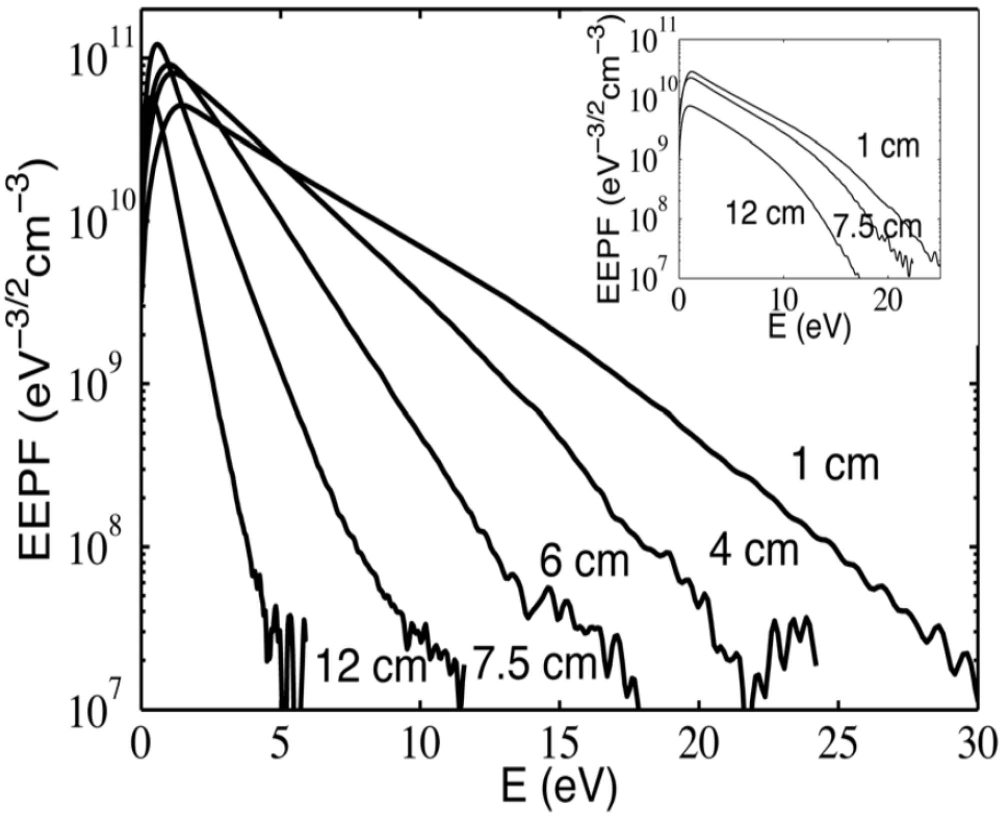
t 40u
Δt 2.5u

Is	8.76E-3	1.17E-2	6.51E-3	1.86E-2	7.85E-3	1.82E-2	5.03E-3
Vp	67	68	64	69	70	68	62
ne(cm^-3)	5.65E+10	8.42E+10	4.33E+10	1.54E+11	4.54E+10	1.58E+11	4.16E+10
Te(eV)	4.73	4.01	4.25	3.15	5.57	2.88	2.94

Time evolution of EEPF in the positive column of Ar dc discharge with moving striations.

p = 10 mTorr, I_d = 1 A. *V. Godyak et al, Presented at GEC 2014, Raleigh, NC, November 2-7 (2014)*

Recently published EEDF measurements with Plasma Sensors instruments



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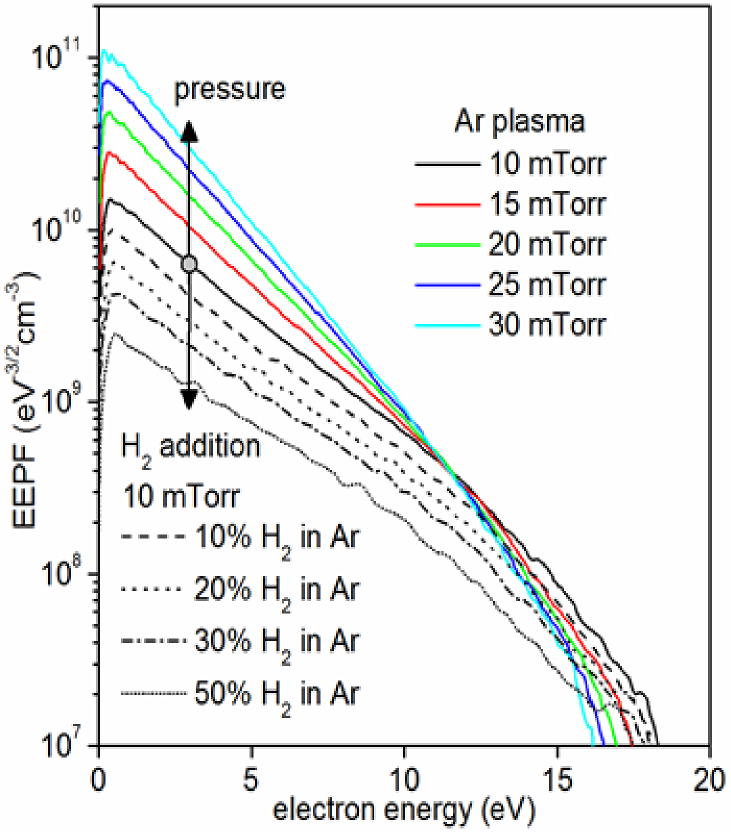
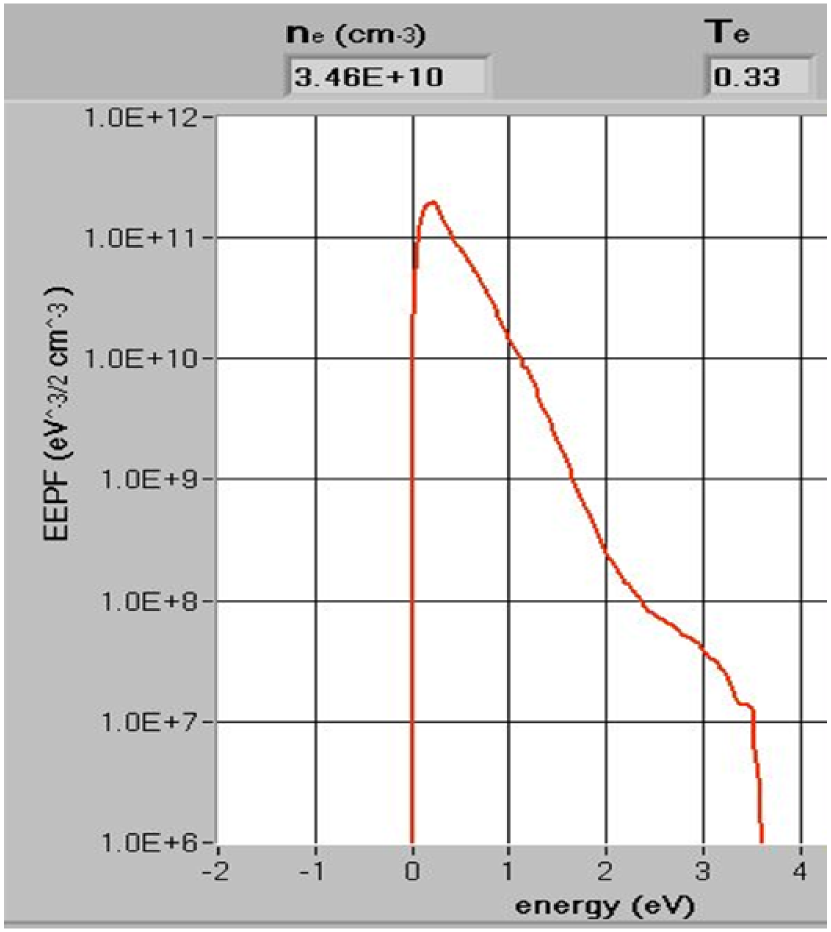


EEPF measured in Ar and Ar/H_2 ICP. *N. Fox-lion et al, J. Phys. D: Appl. Phys,.* ***46,*** *485202, (2013)*

EEDF measured in chemically active plasmas with high deposition rate



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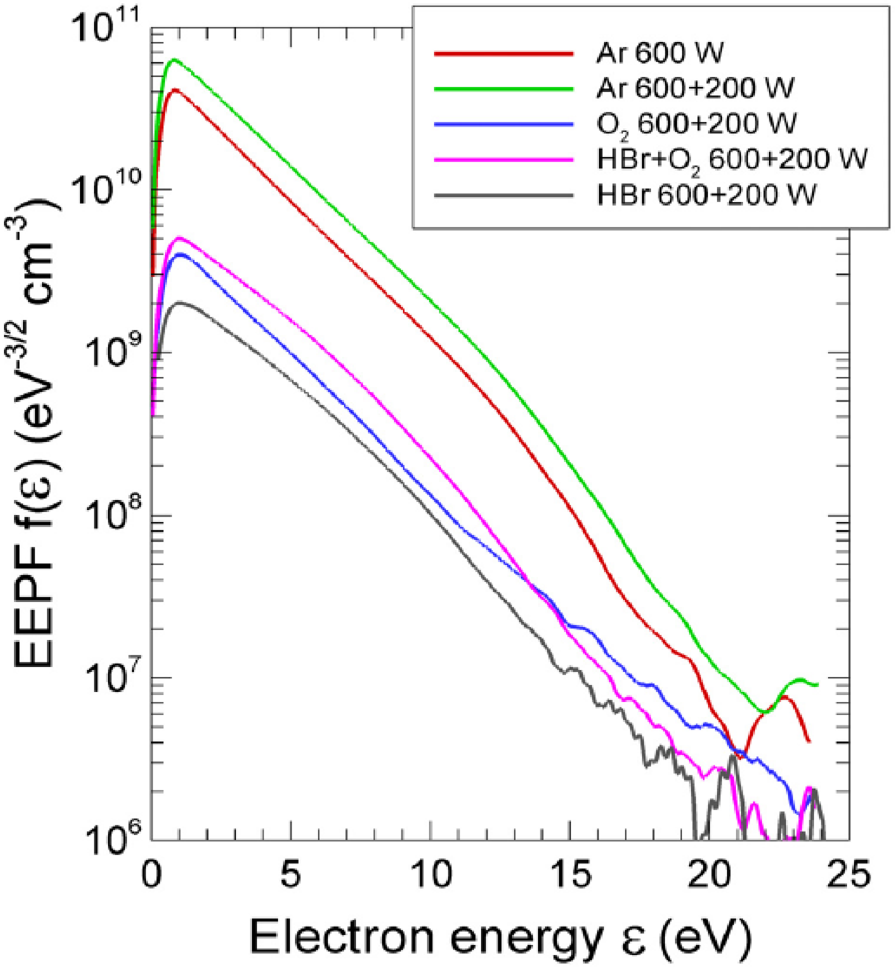
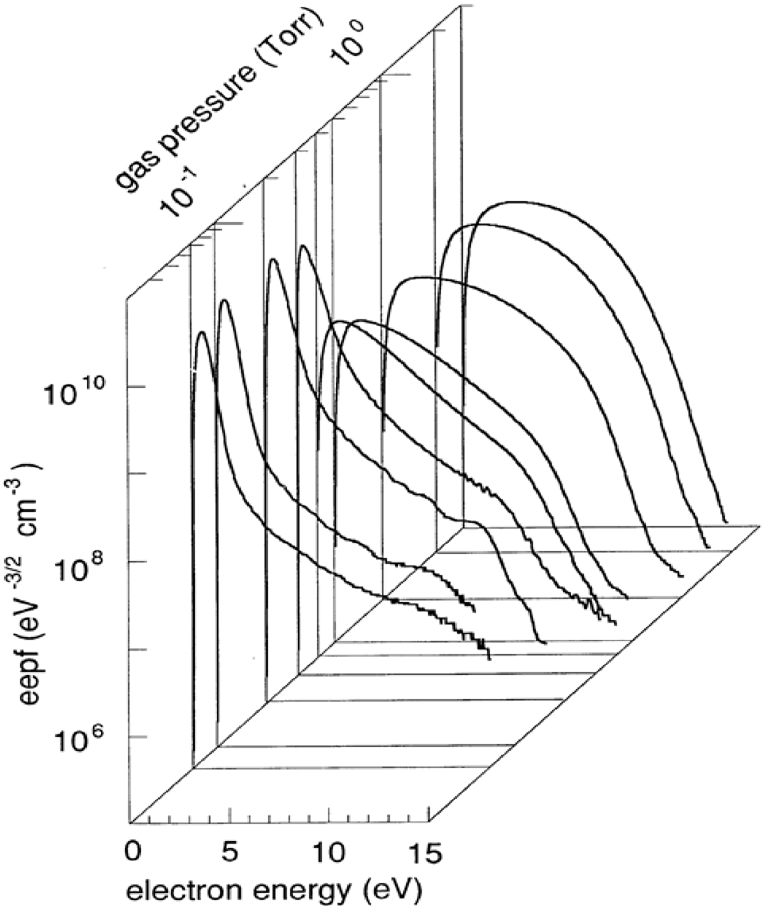
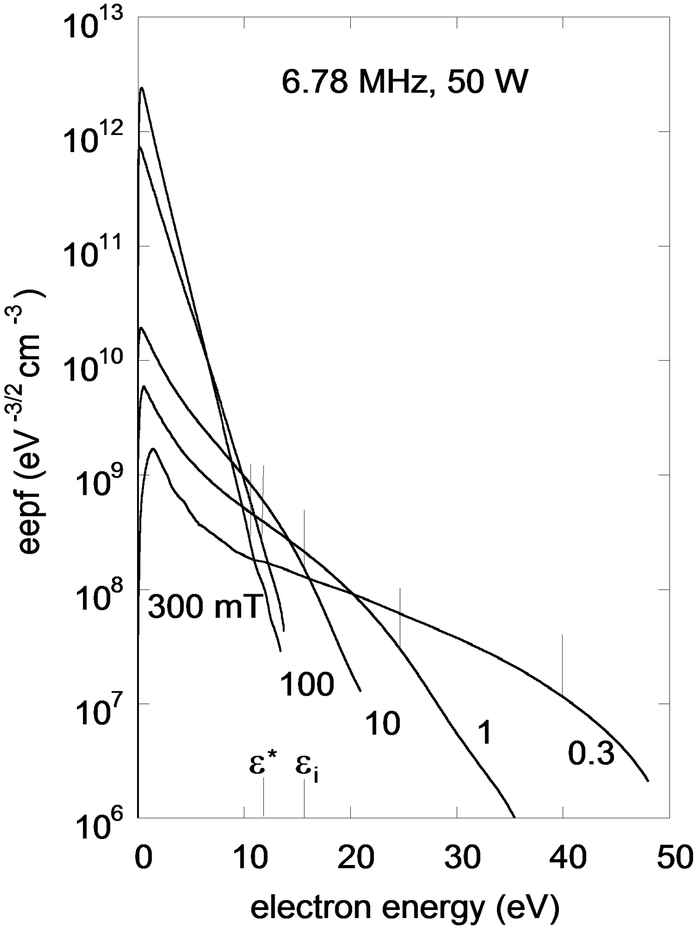


EEPF measured in commercial ICP in different processing mixtures at 15 mTorr. *Mattson Technology, USA*

EEDF measured with Plasma Sensors instruments in basic research experiments



Heating mode transition in Ar CCP,
V. Godyak and R. Piejak,
Phys. Rev. Lett. ***65****, 996 (1990)*



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Sources Sci. Technol. ***11****, 525 (2002)*